

CLAIMS

What is claimed is:

1. A method for forming pi-type bus electrode, said method
5 comprising:

providing a glass substrate;

forming a transparent conductive film with a plurality of cavity
patterns on said glass substrate; and

forming a bus electrode with a pi side on portion of said
10 transparent conductive film layer and on portion of said glass
substrate, said pi side being located on said pattern of cavity.

2. The method according to claim 1, wherein said forming said
transparent conductive film with said plurality of cavity patterns
15 comprises a lithography process.

3. The method according to claim 1, wherein said forming said
transparent conductive film with said plurality of cavity patterns to
expose portion of said glass substrate.
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4. The method according to claim 1, wherein said transparent
conductive film comprises an indium tin oxide (ITO).

5. The method according to claim 1, wherein said method for
25 forming said transparent conductive film comprises a sputtering

method.

6. The method according to claim 1, wherein said method for forming said bus electrode with said pi side comprises:

- 5 forming a conductive layer on said transparent conductive film;
 forming a photoresist layer with a pi pattern on said conductive layer; and
 etching said conductive layer for forming a bus electrode with a pi side.

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7. The method according to claim 6, wherein said method for forming said conductive layer comprises a print method.

8. The method according to claim 1, wherein the material of said
15 conductive layer comprises silver.

9. The method according to claim 8, wherein the material of said conductive layer comprises glass powder.

20 10. A method for improving adhesion capability of electrode, said method comprises:

 providing a glass substrate with a transparent conductive film, wherein said transparent film being located on portion of said glass substrate;

25 forming a photoresist layer with a cavity pattern on said

transparent conductive film;

etching said transparent conductive film and forming a cavity
pattern in said transparent conductive film and forming a transparent
conductive electrode, portion of said glass substrate being exposed
5 from said cavity pattern; and

forming a bus electrode with a pi side on said glass substrate and
on said transparent conductive film, wherein said pi side of said bus
electrode being on said cavity pattern.

10 11. The method according to claim 10, wherein the material of
said transparent conductive film comprises indium tin oxide.

12. The method according to claim 10, wherein said method of
etching said transparent conductive film comprises a wet etching
15 method.

13. The method according to claim 10, wherein said method for
forming said bus electrode with said pi side comprises a print method.

20 14. The method according to claim 10, wherein the material of said
bus electrode with said pi side comprises silver.

15. The method according to claim 14, wherein the material of
said bus electrode with said pi side comprises glass powder.

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16. A method for forming a pi-type bus electrode, said method comprising:

providing a glass substrate;

sputtering a transparent conductive film on said glass substrate;

5 forming a photoresist layer with a cavity pattern on said transparent conductive film;

etching said transparent conductive film to remove portion of said transparent conductive film with said cavity pattern, forming cavity pattern in said transparent conductive film, exposing said glass
10 substrate, and forming a transparent conductive electrode;

printing a conductive layer on said transparent conductive electrode and on said glass substrate;

proceeding lithography step to form a pi-type bus electrode, wherein one pi side of said pi-type bus electrode being in said cavity and
15 on said glass substrate.

17. The method according to claim 16, wherein the material of said transparent conductive film comprises indium tin oxide.

20 18. The method according to claim 16, wherein the material of said conductive layer comprises silver.

19. The method according to claim 18, wherein the material of said conductive layer comprises glass powder.